

1.5V Drive Pch MOSFET

RZQ045P01

●Structure

Silicon P-channel MOSFET

●Features

- 1) Low on-resistance.
- 2) High power package.
- 3) Low voltage drive. (1.5V)

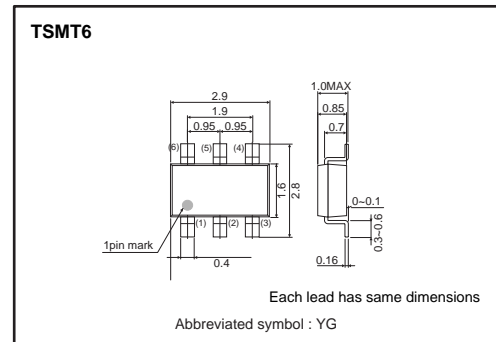
●Applications

Switching

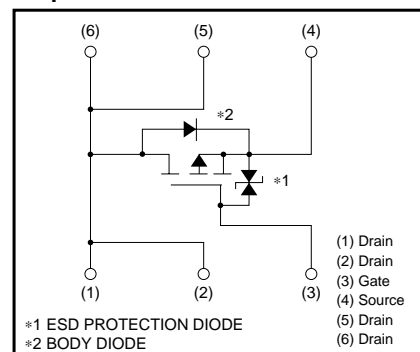
●Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
RZQ045P01		○

●Dimensions (Unit : mm)



●Equivalent circuit



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Drain-source voltage	V_{DS}	-12	V	
Gate-source voltage	V_{GS}	±10	V	
Drain current	Continuous	I_D	±4.5	A
	Pulsed	I_{DP} *1	±12	A
Source current (Body diode)	Continuous	I_S	-1	A
	Pulsed	I_{SP} *1	-12	A
Total power dissipation	P_D *2	1.25	W	
Channel temperature	T_{ch}	150	°C	
Range of Storage temperature	T_{stg}	-55 to +150	°C	

*1 $P_w \leq 10 \mu s$, Duty cycle $\leq 1\%$

*2 Mounted on a ceramic board

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	$R_{th(ch-a)}$ *	100	°C / W

* Mounted on a ceramic board.

Transistors

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	±10	μA	$V_{GS}=\pm 10V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	–12	–	–	V	$I_D = -1mA, V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	–	–	–1	μA	$V_{DS} = -12V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	–0.3	–	–1.0	V	$V_{DS} = -6V, I_D = -1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	–	25	35	mΩ	$I_D = -4.5A, V_{GS} = -4.5V$
		–	31	43	mΩ	$I_D = -2.2A, V_{GS} = -2.5V$
		–	39	58	mΩ	$I_D = -2.2A, V_{GS} = -1.8V$
		–	50	100	mΩ	$I_D = -0.9A, V_{GS} = -1.5V$
Forward transfer admittance	$ Y_{fs} $ *	6.5	–	–	S	$V_{DS} = -6V, I_D = -4.5A$
Input capacitance	C_{iss}	–	2450	–	pF	$V_{DS} = -6V$
Output capacitance	C_{oss}	–	320	–	pF	$V_{GS} = 0V$
Reverse transfer capacitance	C_{rss}	–	290	–	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$ *	–	12	–	ns	$I_D = -2.2A$
Rise time	t_r *	–	75	–	ns	$V_{DD} = -6V$ $V_{GS} = -4.5V$
Turn-off delay time	$t_{d(off)}$ *	–	390	–	ns	$R_L = 2.7\Omega$
Fall time	t_f *	–	215	–	ns	$R_G = 10\Omega$
Total gate charge	Q_g *	–	31	–	nC	$V_{DD} = -6V \quad R_L = 1.3\Omega$
Gate-source charge	Q_{gs} *	–	4.5	–	nC	$V_{GS} = -4.5V \quad R_G = 10\Omega$
Gate-drain charge	Q_{gd} *	–	4.0	–	nC	$I_D = -4.5A$

*Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD} *	–	–	–1.2	V	$I_S = -4.5A, V_{GS} = 0V$

*Pulsed

Transistors

●Electrical characteristic curves

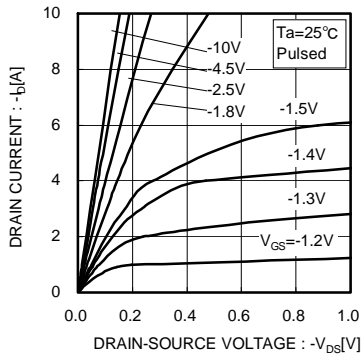


Fig.1 Typical Output Characteristics(I)

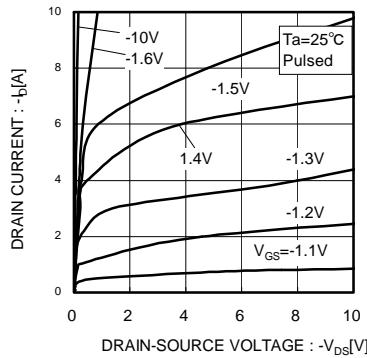


Fig.2 Typical Output Characteristics(II)

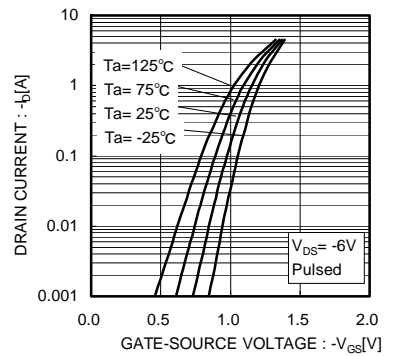


Fig.3 Typical Transfer Characteristics

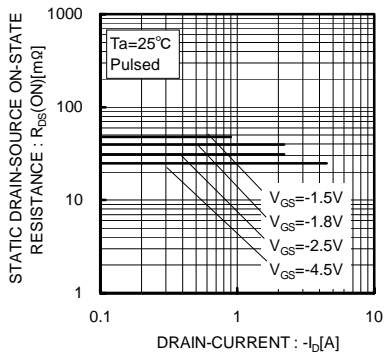


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(I)

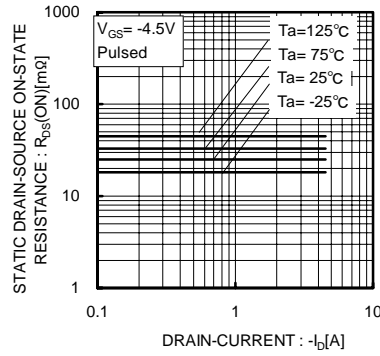


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)

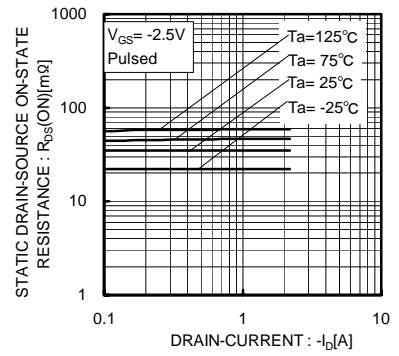


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(III)

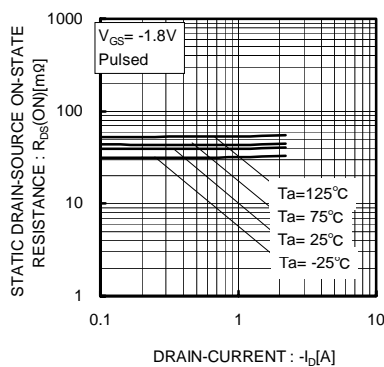


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

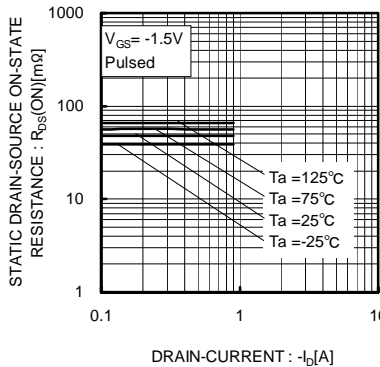


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current(V)

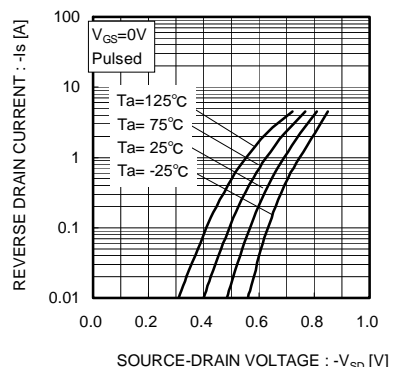


Fig.9 Reverse Drain Current vs. Source-Drain Voltage

Transistors

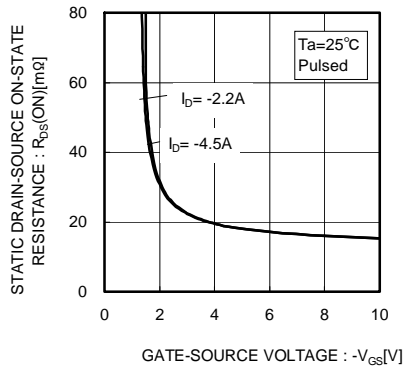


Fig.10 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

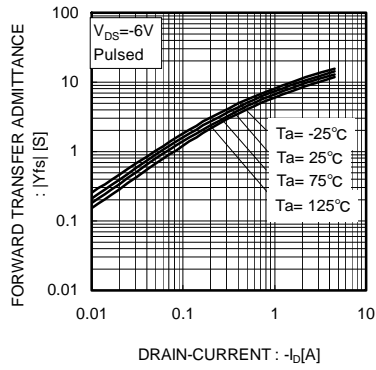


Fig.11 Forward Transfer Admittance vs. Drain Current

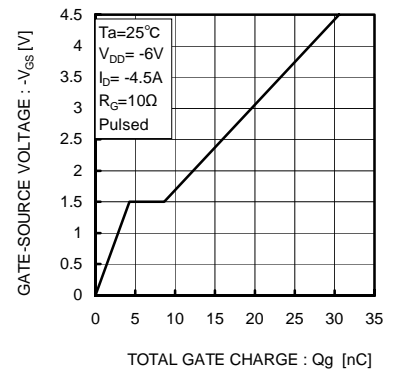


Fig.12 Dynamic Input Characteristics

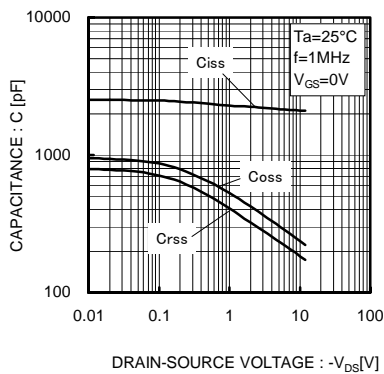


Fig.13 Typical Capacitance vs. Drain-Source Voltage

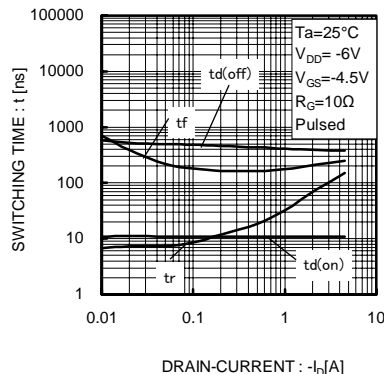


Fig.14 Switching Characteristics

Transistors

●Measurement circuits

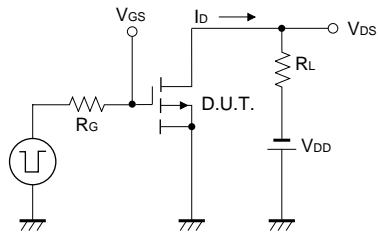


Fig.15 Switching Time Measurement Circuit

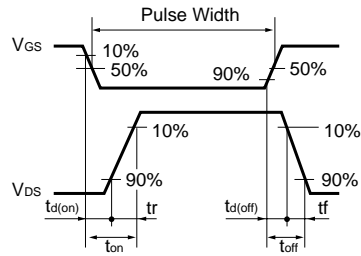


Fig.16 Switching Waveforms

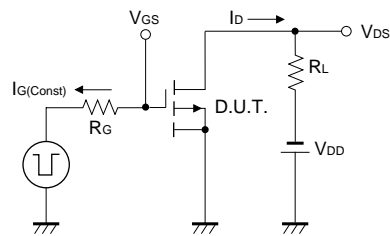


Fig.17 Gate Charge Measurement Circuit

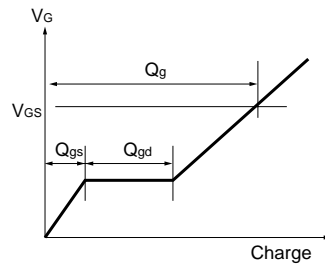


Fig.18 Gate Charge Waveform

●Notice

This product might cause chip aging and breakdown under the large electrified environment .
Please consider to design ESD protection circuit.

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